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Substitute for form 1449/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>				<b>Complete if Known</b>	
				Application Number	
				101622353	
				Filing Date	
				First Named Inventor	
				Erwin J. Prinz	
Group Art Unit					
Examiner Name					
Sheet	1	of	2	Attorney Docket Number	
				SC12852TP	

[illegible][illegible]

Examiner Signature	TAN T. NGUYEN	Date Considered	40/12/04
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EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation, if not in conformance and not considered. Include copy of this form with next communication to applicant.

<sup>1</sup> Unique citation designation number. <sup>2</sup> See Kinds of U.S. Patent Documents. <sup>3</sup> Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). <sup>4</sup> For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. <sup>5</sup> Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. <sup>6</sup> Applicant is to place a check mark here if English Language Translation is attached.

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Substitute for form 1449A/PTO  <b>INFORMATION DISCLOSURE STATEMENT BY APPLICANT</b>  <i>(use as many sheets as necessary)</i>		<i>Complete if Known</i>	
		Application Number	10/622,353
		Filing Date	
		First Named Inventor	Erwin J. Prinz
		Group Art Unit	
Examiner Name			
Sheet 2 of 2	Attorney Docket Number	SC12852TP	

## OTHER PRIOR ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. <sup>1</sup>	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T <sup>2</sup>
TNT	AC	FUJIWARA, I. et al.; "High speed program/erase sub 100 nm MONOS memory cell"; Advanced Devices R&D Laboratories, LSI, SNC, Sony Corporation; pages 75-77	
TNT	AD	CHAN, T.Y. et al.; "A True Single-Transistor Oxide-Nitride-Oxide EEPROM Device"; IEEE Electron Device Letters; March, 1987; pages 93-95; Vol. EDL-8; No. 3	
TNT	AE	Specification; US Patent Application 10/280,294; Craig T. Swift et al.; Filed 10-25-2002	

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